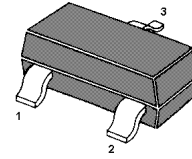


PNP Darlington Transistors

for preamplifier input applications



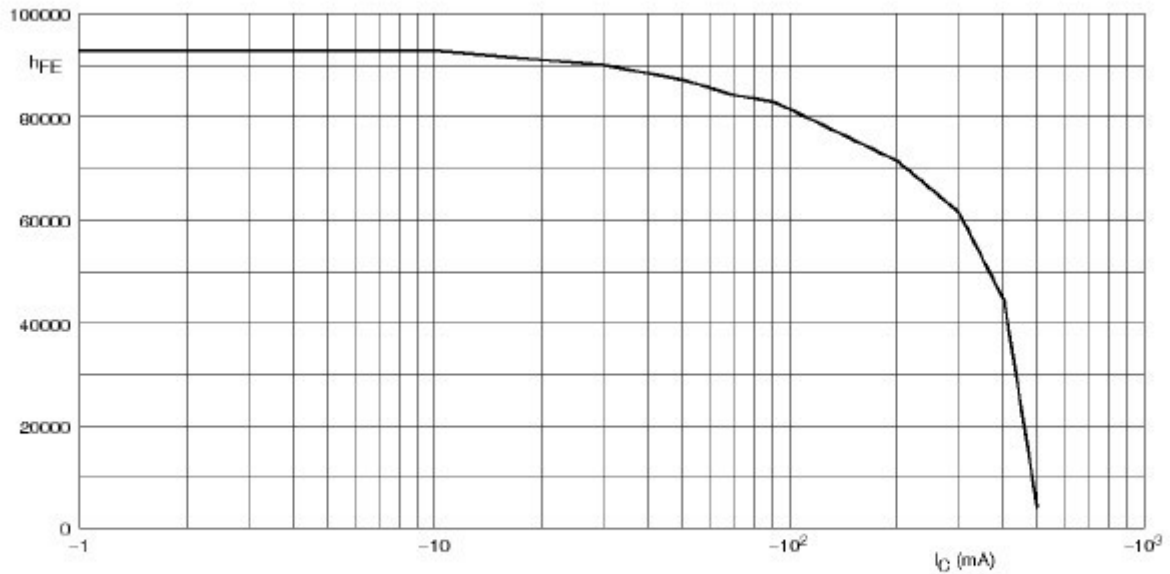
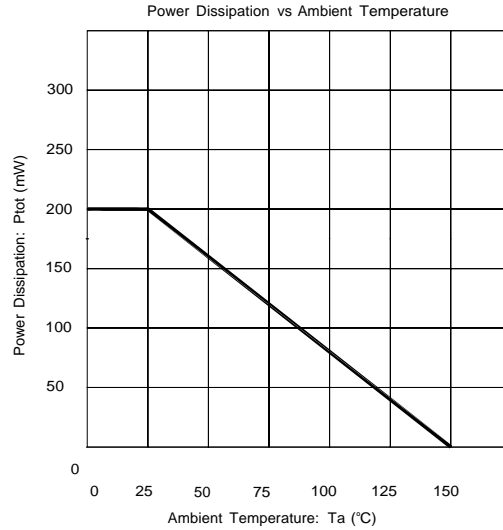
1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	BCV26 BCV46	- V_{CB0}	40 80	V
Collector Emitter Voltage	BCV26 BCV46	- V_{CEO}	30 60	V
Emitter Base Voltage		- V_{EBO}	10	V
Collector Current		- I_C	500	mA
Peak Collector Current		- I_{CM}	800	mA
Base Current		- I_B	100	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_S	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$	BCV26 BCV46	h_{FE}	4000 2000	- -	- -
at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	BCV26 BCV46	h_{FE}	10000 4000	- -	- -
at $-V_{CE} = 5\text{ V}$, $-I_C = 100\text{ mA}$	BCV26 BCV46	h_{FE}	20000 10000	- -	- -
Collector Cutoff Current					
at $-V_{CB} = 30\text{ V}$	BCV26	- I_{CBO}	-	-	100
at $-V_{CB} = 60\text{ V}$	BCV46				100
Emitter Cutoff Current					
at $-V_{EB} = 10\text{ V}$		- I_{EBO}	-	-	100
Collector Base Breakdown Voltage	BCV26 BCV46	- $V_{(BR)CBO}$	40 80	- -	- -
Collector Emitter Breakdown Voltage	BCV26 BCV46	- $V_{(BR)CEO}$	30 60	- -	- -
Emitter Base Breakdown Voltage		- $V_{(BR)EBO}$	10	-	-
Collector Emitter Saturation Voltage		- $V_{CE(sat)}$	-	-	1
at $-I_C = 100\text{ mA}$, $-I_B = 0.1\text{ mA}$					V
Base Emitter Saturation Voltage		- $V_{BE(sat)}$	-	-	1.5
at $-I_C = 100\text{ mA}$, $-I_B = 0.1\text{ mA}$					V
Base Emitter On-state Voltage		- $V_{BE(on)}$	-	-	1.4
at $-I_C = 10\text{ mA}$, $-V_{CE} = 5\text{ V}$					V
Transition Frequency		f_T	-	220	-
at $-V_{CE} = 5\text{ V}$, $-I_C = 30\text{ mA}$, $f = 100\text{ MHz}$					MHz



$V_{CE} = -2V$.

DC current gain; typical values.